

NTJD3158C

Power MOSFET

20 V, +0.63/-0.82 A,
SC-88 Complementary, ESD Protected

Features

- Complementary N- and P-Channel MOSFET
- Small Size Dual SC-88 Package
- Reduced Gate Charge to Improve Switching Response
- Independently Connected Devices to Provide Design Flexibility
- This is a Pb-Free Device

Applications

- DC-DC Conversion Circuits
- Load/Power Switching with Level Shift

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	20	V
Gate-to-Source Voltage			V _{GS}	±12	V
N-Channel Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	I _D	0.63	A
		T _A = 85°C		0.46	
	t ≤ 5 s	T _A = 25°C		0.72	
P-Channel Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	I _D	-0.82	A
		T _A = 85°C		-0.59	
	t ≤ 5 s	T _A = 25°C		-0.93	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	0.27	W
	t ≤ 5 s			0.35	
Pulsed Drain Current	N-Ch	tp = 10 μs	I _{DM}	1.3	A
	P-Ch			-1.6	
Operating Junction and Storage Temperature			T _J , T _{stg}	-55 to 150	°C
Source Current (Body Diode)			I _S	0.46	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	460	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5\text{ s}$ (Note 1)	$R_{\theta JA}$	357	
Junction-to-Lead (Drain) – Steady State (Note 1)	$R_{\theta JL}$	226	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq pad size
(Cu area = 1.127 in sq [1 oz] including traces).

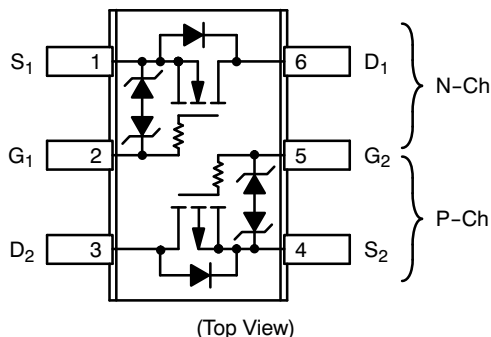


ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)} \text{ Max}$	$I_D \text{ Max}$
N-Ch 20 V	375 m Ω @ 4.5 V	0.63 A
	445 m Ω @ 2.5 V	
P-Ch -20 V	300 m Ω @ -4.5 V	-0.82 A
	500 m Ω @ -2.5 V	

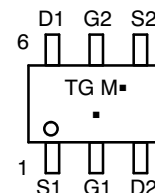
SC-88 (SOT-363)
(6-Leads)



MARKING DIAGRAM & PIN ASSIGNMENT



SC-88 (SOT-363)
CASE 419B
STYLE 26



TG = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTJD3158CT1G	SC-88 (Pb-Free)	3000/Tape & Reel
NTJD3158CT4G	SC-88 (Pb-Free)	10000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTJD3158C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS (Note 3)

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	N	V _{GS} = 0 V	I _D = 250 μA	20		V
		P		I _D = -250 μA	-20		
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				22		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	N	V _{GS} = 0 V, V _{DS} = 16 V			1.0	μA
		P	V _{GS} = 0 V, V _{DS} = -16 V			1.0	
Gate-to-Source Leakage Current	I _{GSS}	N	V _{DS} = 0 V, V _{GS} = ±12 V			±10	μA
		P	V _{DS} = 0 V, V _{GS} = ±4.5 V			±1.0	
		P	V _{DS} = 0 V, V _{GS} = ±12 V		6.0		

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	N	I _D = 250 μA	0.6		1.5	V
		P	I _D = -250 μA	-0.45			
Drain-to-Source On Resistance	R _{DS(on)}	N	V _{GS} = 4.5 V, I _D = 0.63 A		290	375	mΩ
		P	V _{GS} = -4.5 V, I _D = -0.88 A		255	300	
		N	V _{GS} = 2.5 V, I _D = 0.40 A		360	445	
		P	V _{GS} = -2.5 V, I _D = -0.71 A		345	500	
Forward Transconductance	g _{FS}	N	V _{DS} = 4.0 V, I _D = 0.63 A		2.0		S
		P	V _{DS} = -10 V, I _D = -0.88 A		3.0		

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{ISS}	N	f = 1 MHz, V _{GS} = 0 V	V _{DS} = 20 V		33	46	pF
		P		V _{DS} = -20 V		155		
Output Capacitance	C _{OSS}	N		V _{DS} = 20 V		13	22	
		P		V _{DS} = -20 V		25		
Reverse Transfer Capacitance	C _{RSS}	N		V _{DS} = 20 V		2.8	5.0	
		P		V _{DS} = -20 V		18		
Total Gate Charge	Q _{G(TOT)}	N		V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.63 A		1.3	3.0	nC
		P		V _{GS} = -4.5 V, V _{DS} = -15 V, I _D = -0.88 A		2.2		
Gate-to-Source Charge	Q _{GS}	N		V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.63 A		0.2		
		P		V _{GS} = -4.5 V, V _{DS} = -15 V, I _D = -0.88 A		0.5		
Gate-to-Drain Charge	Q _{GD}	N		V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.63 A		0.4		
		P		V _{GS} = -4.5 V, V _{DS} = -10 V, I _D = -0.88 A		0.65		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	N	V _{GS} = 4.5 V, V _{DD} = 10 V, I _D = 0.5 A, R _G = 20 Ω		83		ns
Rise Time	t _r				227		
Turn-Off Delay Time	t _{d(OFF)}				786		
Fall Time	t _f				506		
Turn-On Delay Time	t _{d(ON)}	P	V _{GS} = -4.5 V, V _{DD} = -10 V, I _D = -0.5 A, R _G = 20 Ω		5.8		
Rise Time	t _r				6.5		
Turn-Off Delay Time	t _{d(OFF)}				13.5		
Fall Time	t _f				3.5		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	N	V _{GS} = 0 V, T _J = 25°C	I _S = 0.23 A		0.76	1.1	V
		P		I _S = -0.48 A		-0.8	-1.2	
		N	V _{GS} = 0 V, T _J = 125°C	I _S = 0.23 A		0.63		
		P		I _S = -0.48 A		-0.66		

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES (N-Ch) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

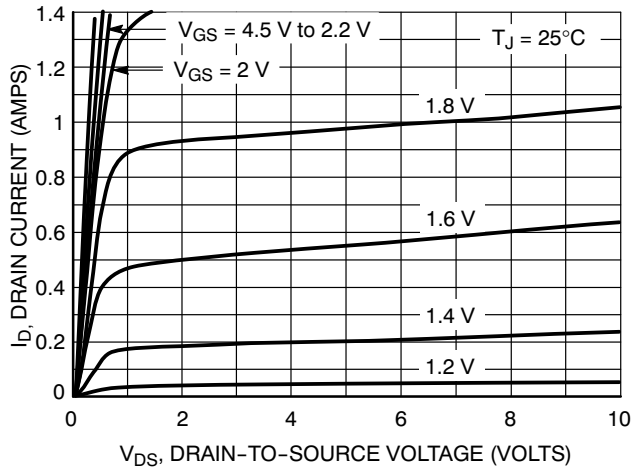


Figure 1. On-Region Characteristics

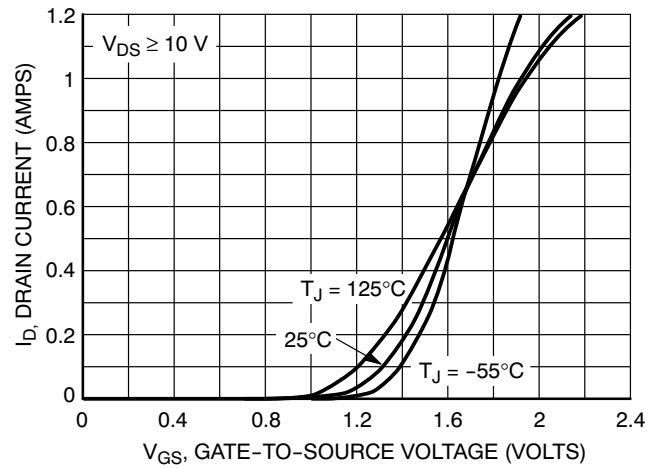


Figure 2. Transfer Characteristics

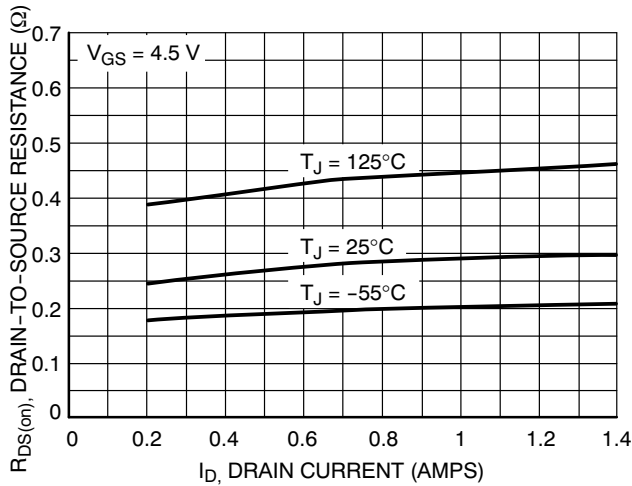


Figure 3. On-Resistance vs. Drain Current and Temperature

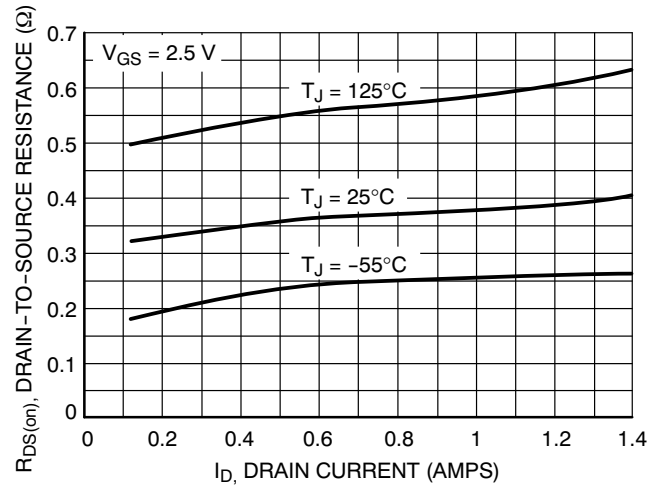


Figure 4. On-Resistance vs. Drain Current and Temperature

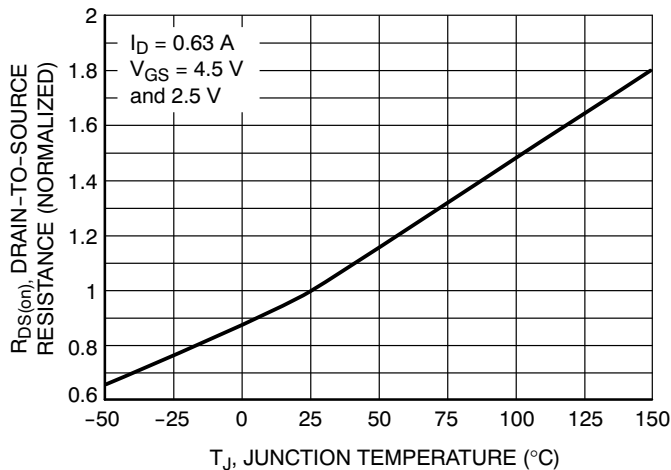


Figure 5. On-Resistance Variation with Temperature

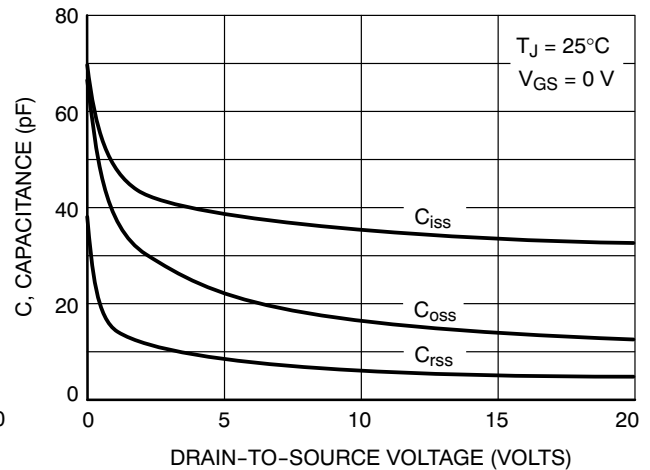


Figure 6. Capacitance Variation

TYPICAL PERFORMANCE CURVES (N-Ch) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

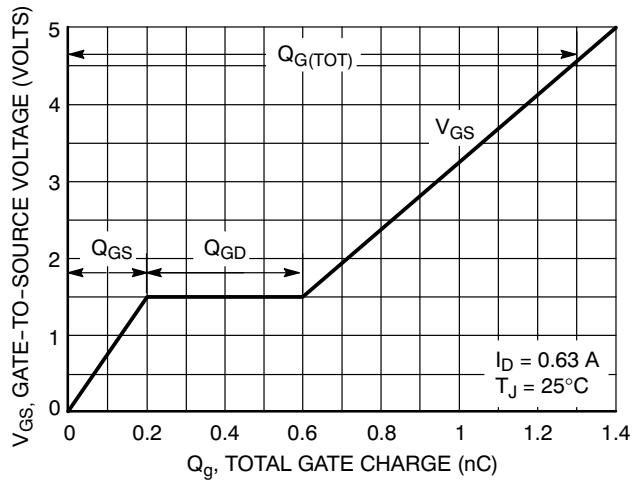


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

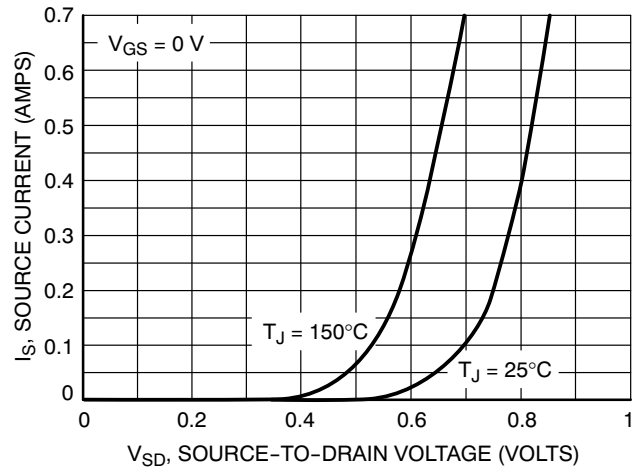


Figure 8. Diode Forward Voltage vs. Current

TYPICAL PERFORMANCE CURVES (P-Ch) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

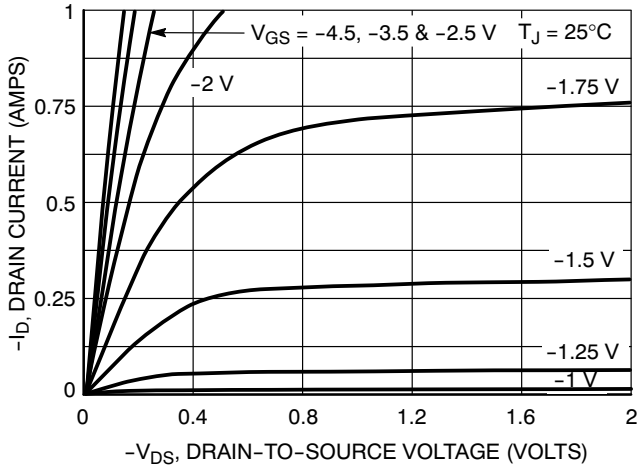


Figure 9. On-Region Characteristics

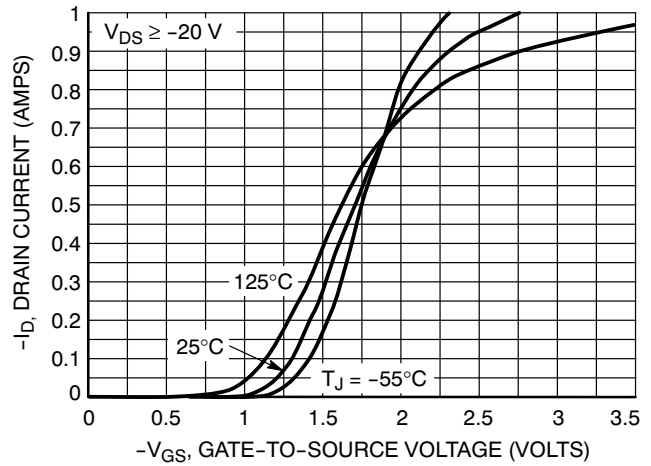


Figure 10. Transfer Characteristics

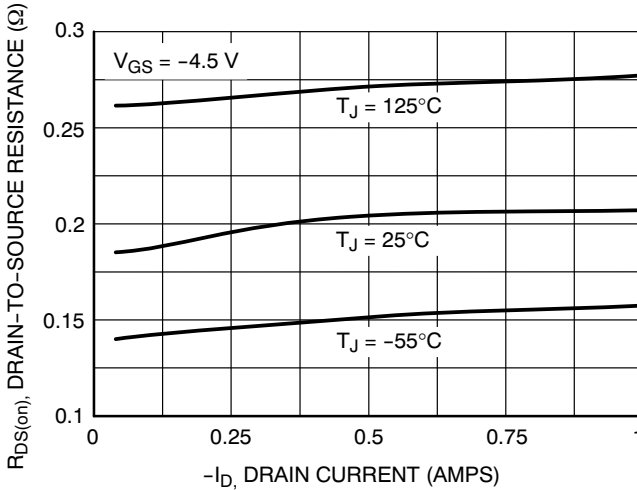


Figure 11. On-Resistance vs. Drain Current and Temperature

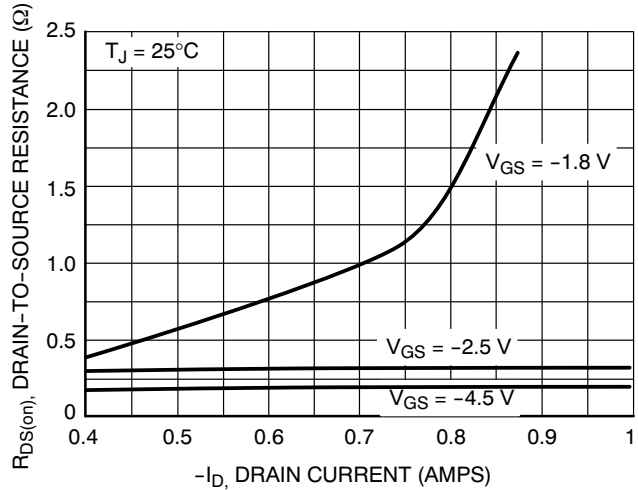


Figure 12. On-Resistance vs. Drain Current and Gate Voltage

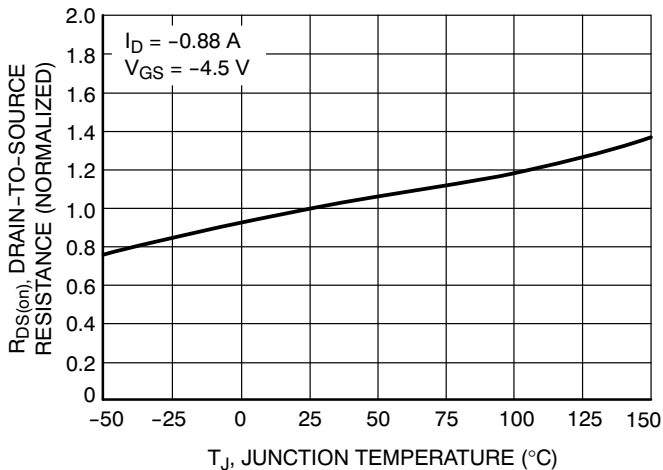


Figure 13. On-Resistance Variation with Temperature

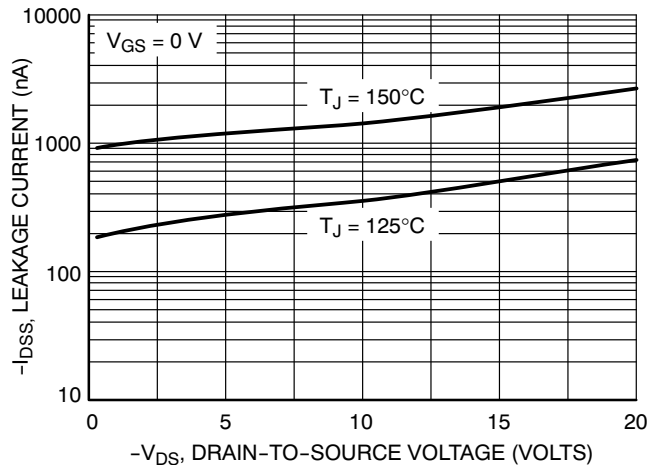
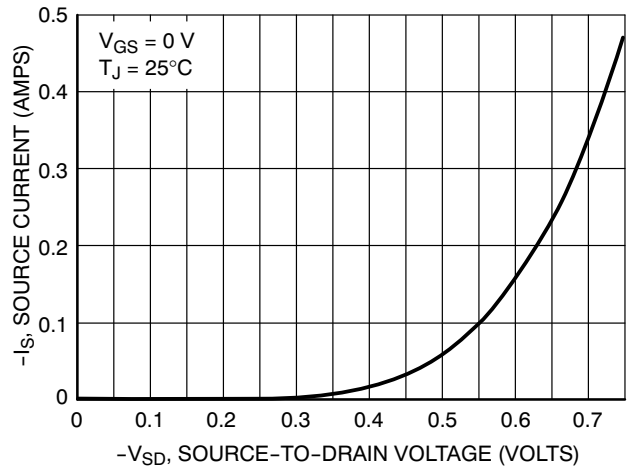
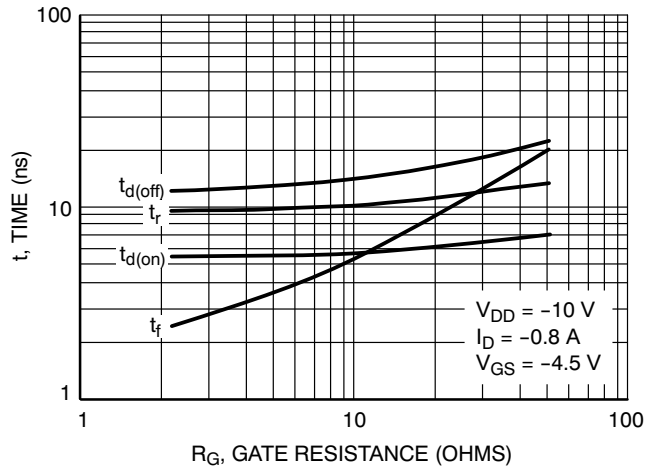
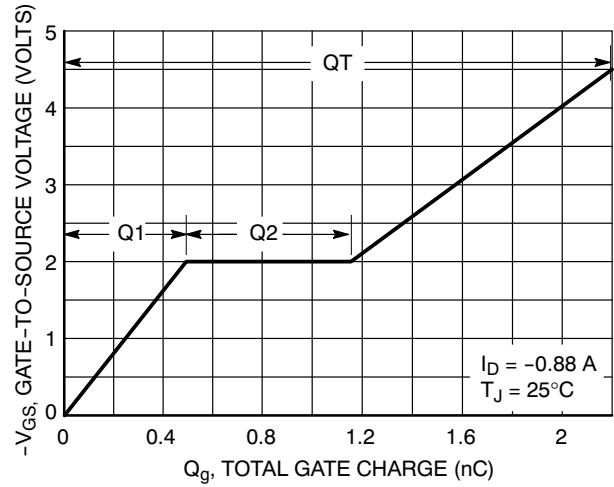
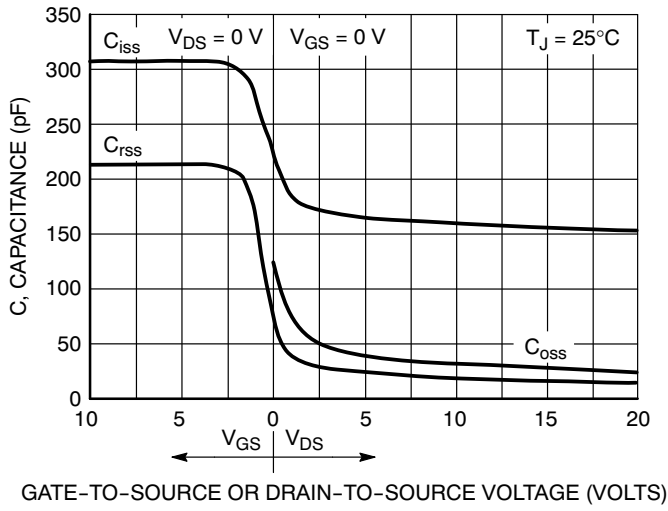


Figure 14. Drain-to-Source Leakage Current vs. Voltage

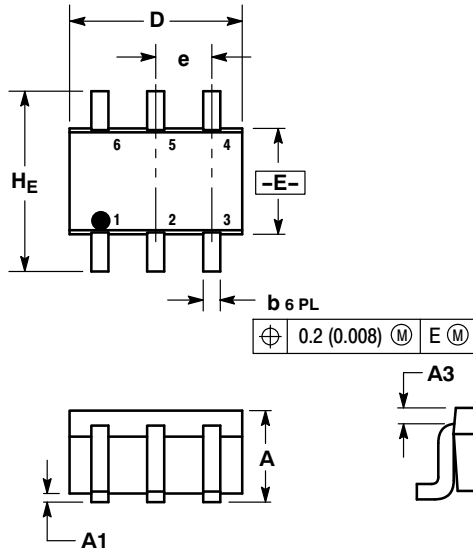
TYPICAL PERFORMANCE CURVES (P-Ch) ($T_J = 25^\circ\text{C}$ unless otherwise noted)



NTJD3158C

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE W

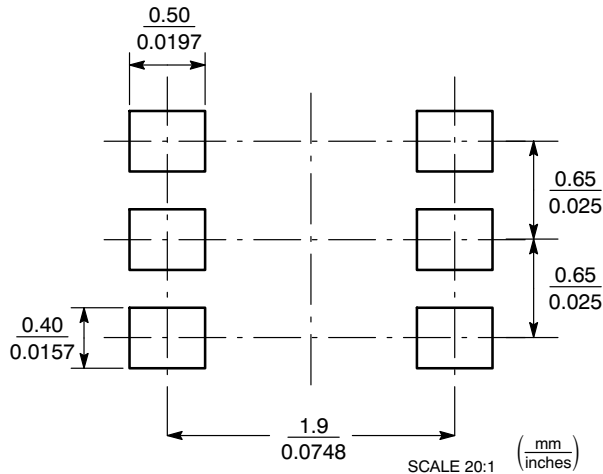


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

- STYLE 26:
- PIN 1. SOURCE 1
 - GATE 1
 - DRAIN 2
 - SOURCE 2
 - GATE 2
 - DRAIN 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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